

IN THE CLAIMS

1. (Currently Amended) A semiconductor laser light emitting device comprising:

~~a stacked film composed of~~ a stack of group III nitride semiconductor films;

wherein each containing at least one kind group III nitride semiconductor film

comprises an element selected from the group consisting of aluminum, gallium, indium, and

boron;

wherein, an upper portion of said stacked film stack of group III nitride

semiconductor films comprises is formed into a ridge like stripe, to form a current injection

region;

wherein a current injection width Wst of said current injection region is at a value

in a range of $1 \mu\text{m} \leq Wst \leq 3 \mu\text{m}$; and

wherein said current injection region is formed on an active layer;

a current non-injection region formed on both sides of said ridge like strip current

injection region, wherein [;] at least part of said current non-injection region comprises is made

from a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1.0$), wherein the

component ratio "x" of Al is at a value in a range of $0.3 \leq x \leq 1.0$, so that said semiconductor

laser light emitting device is configured as an index guide type semiconductor laser light

emitting device; and

wherein the group III nitride semiconductor films a film located between an the active

layer and the current non-injection region of the stacked film made from, comprises a material

expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0.3 \leq x \leq 1.0$), and has have a combined thickness

of less than or equal to $0.2 \mu\text{m}$ but greater than zero.

Claims 2-4 (Cancelled)

5. (Original) A semiconductor laser light emitting device according to claim 1, wherein a difference Δn between an effective refractive index n_1 of said current injection region in the film stacking direction and an effective refractive index n_2 of said current non-injection region in the film stacking direction is in a range of $0.007 \leq \Delta n = (n_1 - n_2) \leq 0.012$.

Claims 6-8 (Cancelled)

9. (Currently Amended) A semiconductor laser light emitting device comprising: ~~a stacked film composed of~~ a stack of group III nitride semiconductor films; wherein each containing at least one kind group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron; wherein, an upper portion of said ~~stacked film~~ stack of group III nitride semiconductor films comprises is formed into a ridge-like stripe, to form a current injection region; wherein a current injection width Wst of said current injection region is at a value in a range of $1 \mu\text{m} \leq Wst \leq 3 \mu\text{m}$; and wherein said current injection region is formed on an active layer; a current non-injection region formed on both sides of said ~~ridge-like strip~~ current injection region, wherein [[;]] and at least part of said current non-injection region comprises is

~~made from~~ a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leq x \leq 1.0$);, wherein the

component ratio "x" of Al is at a value in a range of $0.15 < x < 0.30$ [[,]]

~~so that said semiconductor laser light emitting device is configured as a weak index type~~

~~pulsation semiconductor laser light emitting device; and~~

wherein the group III nitride semiconductor films a film located between ~~an~~ the active layer and the current non-injection region ~~of the stacked film made from,~~ comprises a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0.15 \leq x \leq 0.30$), and ~~has~~ have a combined thickness of less than or equal to $0.2 \mu m$ but greater than zero.

Claims 10-12 (Cancelled)

13. (Original) A semiconductor laser light emitting device according to claim 9, wherein a difference Δn between an effective refractive index $n1$ of said current injection region in the film stacking direction and an effective refractive index $n2$ of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

Claims 14-24 (Cancelled)

25. (Currently Amended) A semiconductor laser light emitting device comprising: a stack of group III nitride semiconductor films each comprising at least one element selected from the group of aluminum, gallium, indium, and boron;

an upper portion of said ~~stacked film~~ stack of group III nitride semiconductor films comprises forming a ridge-like stripe for a current injection region; wherein a current non-injection region formed on both sides of said ridge-like strip, wherein ~~at least part of~~ said current non-injection region comprises ~~is made from~~ a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leq x \leq 1.0$), and wherein the component ratio "x" of Al is between 0.3 and 1.0; and a p-side electrode ~~is~~ formed on and in contact with the current non-injection region.

26. (Currently Amended) A semiconductor laser light emitting device comprising:
a stack of group III nitride semiconductor films each comprising at least one element selected from the group of aluminum, gallium, indium, and boron;
an upper portion of said stacked film forming a ridge-like stripe for a current injection region; a current non-injection region formed on both sides of said ridge-like strip, wherein at least part of said current non-injection region is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leq x \leq 1.0$), and wherein the component ratio "x" of Al is between 0.3 and 1.0; and a contact layer formed ~~in between~~ on the current injection region, wherein the current non-injection region is formed on both sides of said contact layer.

27. (Previously Presented) A semiconductor laser light emitting device according to claim 26, wherein the contact layer is formed on the ridge-like stripe.

28. (Previously Presented) A semiconductor laser light emitting device

according to claim 27, wherein the contact layer is in contact with the ridge-like stripe.

29. (Previously Presented) A semiconductor laser light emitting device

according to claim 26, further comprising a p-side electrode is formed on and in contact with the contact layer.

30. (Currently Amended) A semiconductor laser light emitting device comprising:

a stack of group III nitride semiconductor films;

wherein each group III nitride semiconductor film comprises an element selected from the group consisting of comprising at least one element selected from the group of aluminum, gallium, indium, and boron;

wherein, an upper portion of said stacked film stack of group III nitride semiconductor films comprises forming a ridge-like stripe for a current injection region;

wherein a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein at least part of said current non-injection region comprises is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leq x \leq 1.0$); and

wherein the group III nitride semiconductor films a film located between an the active layer and the current non-injection region of the stacked film made from, comprises a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0.15 \leq x \leq 0.30$), and having have a combined thickness of less than or equal to $0.2 \mu m$ but greater than zero.